

# **BUK7Y12-40E**

# N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK56 9 May 2013 Product data sheet

### 1. General description

Standard level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> rating of greater than 1 V at 175 °C

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- · Ultra high performance power switching

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	52	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	65	W	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11		-	9.3	12	mΩ	
Dynamic characteristics								
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; V_{DS} = 32 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	5.2	-	nC	



#### N-channel 40 V, 12 m $\Omega$ standard level MOSFET in LFPAK56

### 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	[q]	G_UN4)
4	G	gate	و ق ق ق	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

### 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK7Y12-40E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

### 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7Y12-40E	71240E

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$	-	40	V
$V_{DGR}$	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	40	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC	-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	52	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	37	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4	-	210	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	65	W
T <sub>stg</sub>	storage temperature		-55	175	°C

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#### N-channel 40 V, 12 m $\Omega$ standard level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain	diode					,
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	52	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$		-	210	Α
Avalanche rug	ggedness					,
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 52 A; $V_{sup} \le$ 40 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[1][2]	-	22.75	mJ

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.

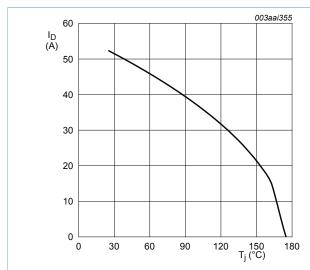


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$ 

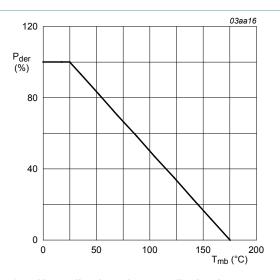


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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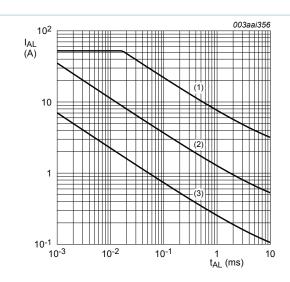
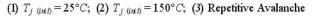


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



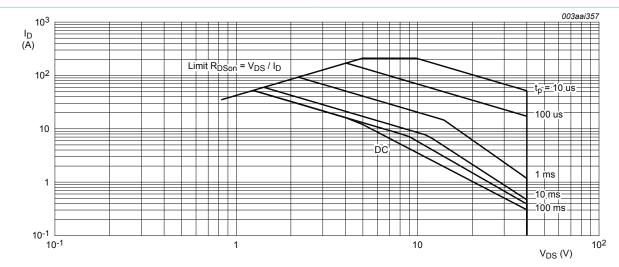


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

#### 9. Thermal characteristics

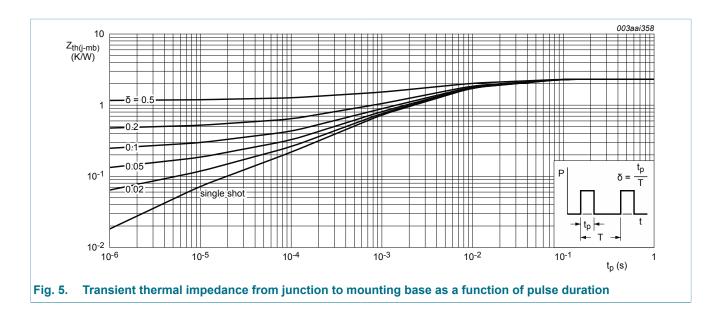
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	2.31	K/W

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#### N-channel 40 V, 12 m $\Omega$ standard level MOSFET in LFPAK56



### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V
I <sub>DSS</sub> drain	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.56	1	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 15 A; $T_{j}$ = 25 °C; Fig. 11	-	9.3	12	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	23.6	mΩ
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V;	-	15	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	4.2	-	nC
$Q_{GD}$	gate-drain charge		-	5.2	-	nC

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#### N-channel 40 V, 12 m $\Omega$ standard level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 15}}$		-	779	1039	pF
C <sub>oss</sub>	output capacitance			-	176	211	pF
C <sub>rss</sub>	reverse transfer capacitance			-	114	156	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}\text{C}$		-	6	-	ns
t <sub>r</sub>	rise time			-	7	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	10	-	ns
t <sub>f</sub>	fall time			-	6	-	ns
Source-dra	in diode	1	l		-		
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 15 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>		-	0.86	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S$ = 15 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 25 V; $T_j$ = 25 °C		-	15.3	-	ns
Q <sub>r</sub>	recovered charge			-	7.4	-	nC

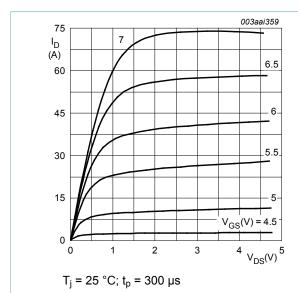


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

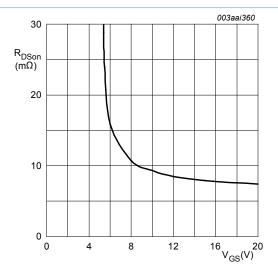


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C;  $I_D = 15A$ 

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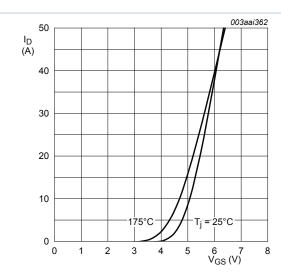


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



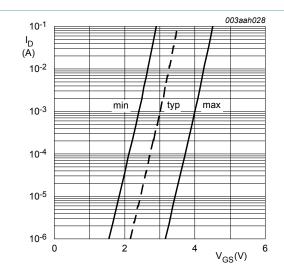


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C;  $V_{DS} = 5V$ 

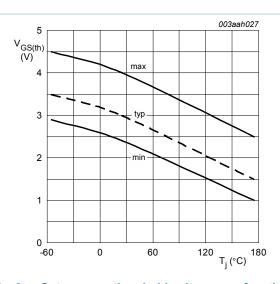
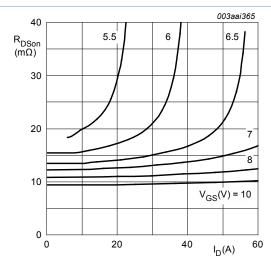


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1$$
 mA;  $V_{DS} = V_{GS}$ 



 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$ 

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

#### N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK56

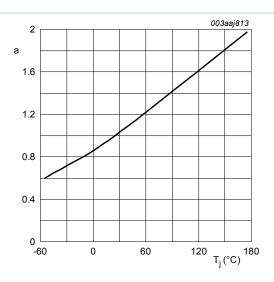


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

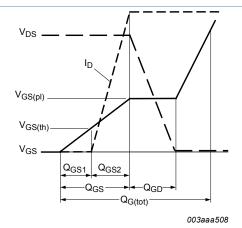


Fig. 14. Gate charge waveform definitions

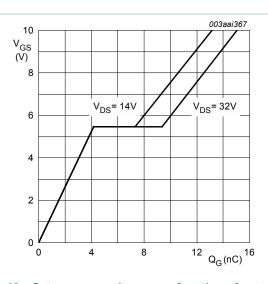


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; \ I_D = 15A$$

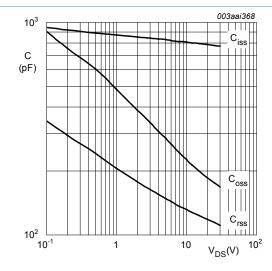


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

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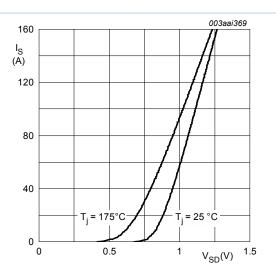


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

#### N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK56

### 11. Package outline

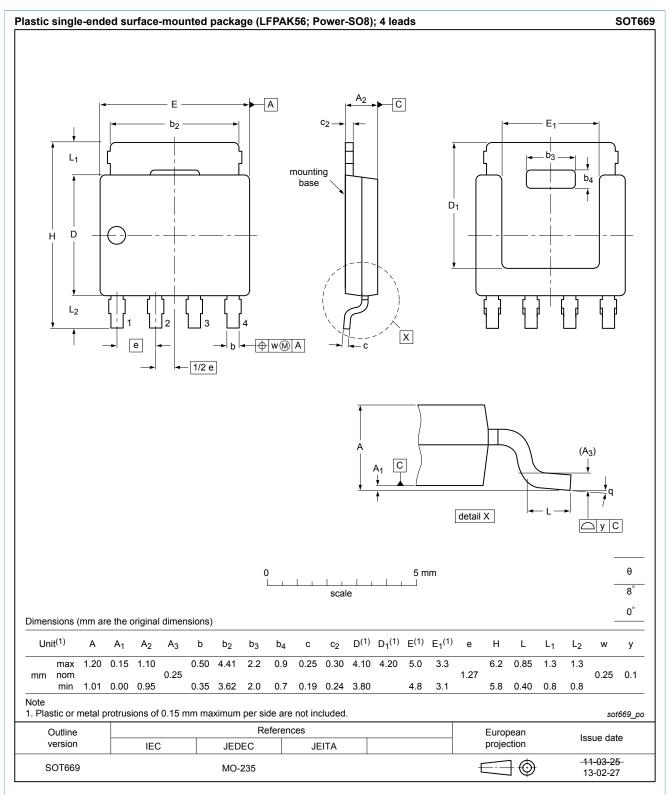


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

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